

C Microsemi.

APT20SCD65K

650V 20A

Zero Recovery Silicon Carbide Schottky Diode

PRODUCT APPLICATIONS

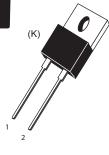
- Anti-Parallel Diode
 -Switchmode Power Supply
 -Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Time (t_{rr})
- Popular TO-220 Package
- Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates
 snubber





1 - Cathode 2 - Anode Back of Case - Cathode

 T_{C} = 25°C unless otherwise specified.

MAXIMUM RATINGS

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage			Volts	
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		650		
V _{RWM}	Maximum Working Peak Reverse Voltage				
I _F	Maximum D.C. Forward Current	T _c = 25°C	32		
		T _c = 90°C	20		
I _{FRM}	Repetitive Peak Forward Surge Current (T _c = 25°C, t _p = 10ms, Half Sine Wave)		75	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current ($T_c = 25^{\circ}C$, $t_p = 10$ ms, Half Sine)		165		
P _{TOT}	Power Dissipation	T _c = 25°C	114	w	
		T _c = 110°C	36		
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to 150	°C	
TL	Lead Temperature for 10 Seconds		300	C	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		Min	Тур	Мах	Unit
V _F	Forward Voltage	I _F = 20A T _J = 25°C		1.5	1.8	Volts
		I _F = 20A, T _J = 150°C		1.9		
I _{RM}	Maximum Reverse Leakage Current	V _R = 650V T _J = 25°C		20	400	μΑ
		V _R = 650V, T _J = 150°C		250		
Q _c	Total Capactive Charge V _R = 325V, I _F = 20A, di/dt = -500A/µs, T _J = 25°C			100		nC
C _T	Junction Capacitance $V_{R} = 0.1V$, $T_{J} = 25^{\circ}C$, f = 1MHz			680		pF
	Junction Capacitance V_{R} = 200V, T _J = 25°C, f = 1MHz			89		
	Junction Capacitance V_{R} = 400V, T_{J} = 25°C, f = 1MHz			73]

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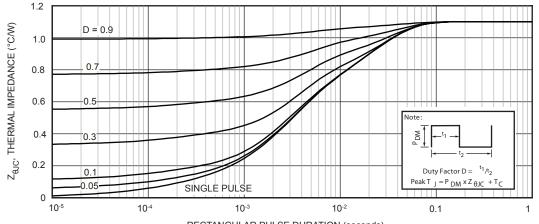
THERMAL AND MECHANICAL CHARACTERISTICS

APT20SCD65K

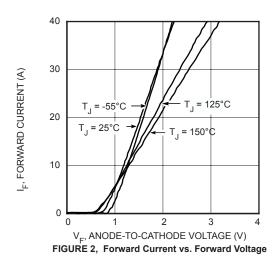
Symbol	Characteristic / Test Conditions	Min	Тур	Мах	Unit
R _{ejc}	Junction-to-Case Thermal Resistance			1.1	°C/W
W _T	Package Weight		0.07		oz
			1.9		g
Torque	Maximum Mounting Torque			6.4	lb∙in
				0.7	N∙m

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TYPICAL PERFORMANCE CURVES



RECTANGULAR PULSE DURATION (seconds) FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



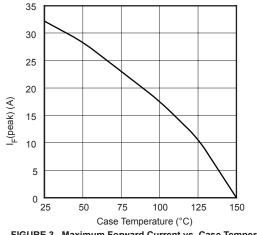
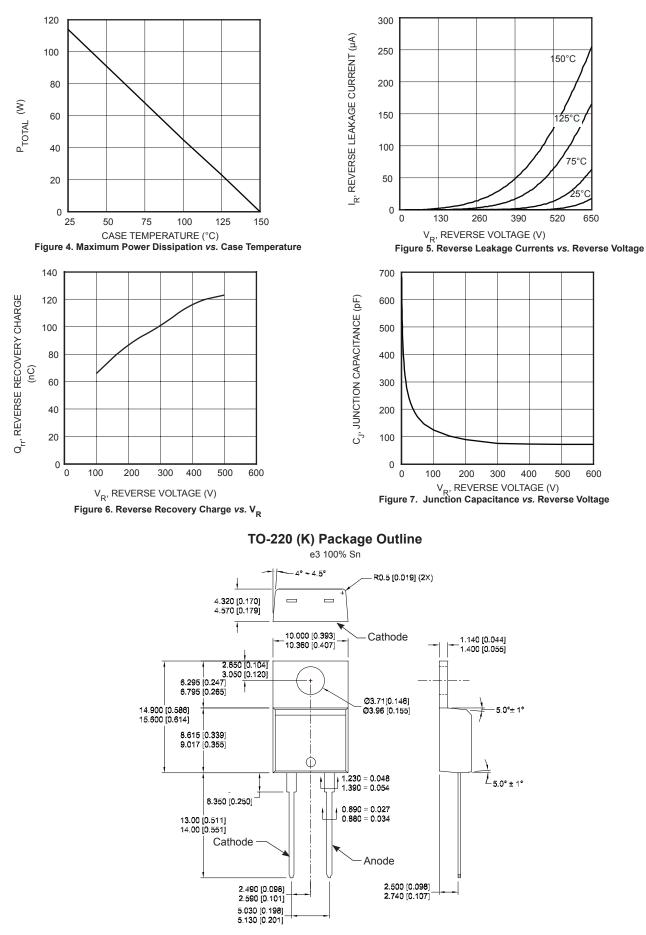


FIGURE 3, Maximum Forward Current vs. Case Temperature



Dimensions in millimeters and [inches]

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